Michael Jetter

List of Publications by Year
in descending order

220 papers	3,602 citations	126907 33 h-index	182427 51 g-index
229 all docs	229 docs citations	229 times ranked	3109 citing authors

#	Article	IF	Citations
1	Visible-to-Telecom Quantum Frequency Conversion of Light from a Single Quantum Emitter. Physical Review Letters, 2012, 109, 147404.	7.8	207
2	Detuning-dependent Mollow triplet of a coherently-driven single quantum dot. Optics Express, 2013, 21, 4382.	3.4	132
3	Cascaded single-photon emission from the Mollow triplet sidebands of a quantum dot. Nature Photonics, 2012, 6, 238-242.	31.4	128
4	Band-gap measurements of direct and indirect semiconductors using monochromated electrons. Physical Review B, 2007, 75, .	3.2	103
5	Single-photon emission at 1.55 <i>Î¼</i>m from MOVPE-grown InAs quantum dots on InGaAs/GaAs metamorphic buffers. Applied Physics Letters, 2017, 111, .	3.3	95
6	Differential phase contrast 2.0â€"Opening new â€œfieldsâ€•for an established technique. Ultramicroscopy, 2012, 117, 7-14.	1.9	86
7	Two-photon interference in the telecom C-band after frequency conversion of photons from remote quantum emitters. Nature Nanotechnology, 2019, 14, 23-26.	31.5	82
8	Quantum key distribution using quantum dot single-photon emitting diodes in the red and near infrared spectral range. New Journal of Physics, 2012, 14, 083001.	2.9	80
9	Ultra-sensitive mid-infrared evanescent field sensors combining thin-film strip waveguides with quantum cascade lasers. Analyst, The, 2012, 137, 2322.	3.5	70
10	Optical and structural properties of InP quantum dots embedded in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mrow><mml:mo>(</mml:mo><mml:mrow><mml:msub><mml:mrow><m Physical Review B, 2009, 79, .	3.2	68
11	InP/AlGaInP quantum dot laser emitting at 638nm. Journal of Crystal Growth, 2011, 315, 123-126.	1.5	65
12	Semiconductor membrane external-cavity surface-emitting laser (MECSEL). Optica, 2016, 3, 1506.	9.3	63
13	Threeâ€dimensional GaN for semipolar light emitters. Physica Status Solidi (B): Basic Research, 2011, 248, 549-560.	1.5	62
14	Fully On-Chip Single-Photon Hanbury-Brown and Twiss Experiment on a Monolithic Semiconductorâ€"Superconductor Platform. Nano Letters, 2018, 18, 6892-6897.	9.1	61
15	Phonon-assisted incoherent excitation of a quantum dot and its emission properties. Physical Review B, 2012, 86, .	3.2	60
16	Polarization-entangled photons from an InGaAs-based quantum dot emitting in the telecom C-band. Applied Physics Letters, 2017, 111, .	3.3	60
17	Combining in-situ lithography with 3D printed solid immersion lenses for single quantum dot spectroscopy. Scientific Reports, 2017, 7, 39916.	3.3	57
18	Electrically driven quantum dot single-photon source at 2â€‰GHz excitation repetition rate with ultra-low emission time jitter. Applied Physics Letters, 2013, 102, .	3.3	48

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19	Mid-Infrared Spectroscopy Platform Based on GaAs/AlGaAs Thin-Film Waveguides and Quantum Cascade Lasers. Analytical Chemistry, 2016, 88, 2558-2562.	6.5	48
20	Coherence and indistinguishability of highly pure single photons from non-resonantly and resonantly excited telecom C-band quantum dots. Applied Physics Letters, 2019, 115, .	3.3	48
21	InAs quantum dots grown on metamorphic buffers as non-classical light sources at telecom C-band: a review. Semiconductor Science and Technology, 2019, 34, 053001.	2.0	47
22	Semiconductor Quantum Dots for Integrated Quantum Photonics. Advanced Quantum Technologies, 2019, 2, 1900020.	3.9	45
23	Simultaneous Faraday filtering of the Mollow triplet sidebands with the Cs-D1 clock transition. Nature Communications, 2016, 7, 13632.	12.8	43
24	Near-red emission from site-controlled pyramidal InGaN quantum dots. Applied Physics Letters, 2005, 87, 163121.	3.3	41
25	Structural and optical properties of InAs/(In)GaAs/GaAs quantum dots with single-photon emission in the telecom C-band up to 77 K. Physical Review B, 2018, 98, .	3.2	41
26	Influence of the Dark Exciton State on the Optical and Quantum Optical Properties of Single Quantum Dots. Physical Review Letters, 2008, 101, 146402.	7.8	40
27	Bright Purcell Enhanced Single-Photon Source in the Telecom O-Band Based on a Quantum Dot in a Circular Bragg Grating. Nano Letters, 2021, 21, 7740-7745.	9.1	39
28	Electrically pumped single-photon emission in the visible spectral range up to 80 K. Optics Express, 2008, 16, 12771.	3.4	38
29	Reducing vortex losses in superconducting microwave resonators with microsphere patterned antidot arrays. Applied Physics Letters, 2012, 100, .	3.3	38
30	Monolithic on-chip integration of semiconductor waveguides, beamsplitters and single-photon sources. Journal Physics D: Applied Physics, 2015, 48, 085101.	2.8	36
31	Metal-organic vapor-phase epitaxy-grown ultra-low density InGaAs/GaAs quantum dots exhibiting cascaded single-photon emission at 1.3â€‰<i>Î¼</i>m. Applied Physics Letters, 2015, 106, .	3.3	36
32	Mode-locked red-emitting semiconductor disk laser with sub-250 fs pulses. Applied Physics Letters, 2013, 103, .	3.3	35
33	Deterministic integration and optical characterization of telecom O-band quantum dots embedded into wet-chemically etched Gaussian-shaped microlenses. Applied Physics Letters, 2018, 113, .	3.3	33
34	Electronic shell structure and carrier dynamics of high aspect ratioInPsingle quantum dots. Physical Review B, 2007, 75, .	3.2	31
35	Quantitative measurements of internal electric fields with differential phase contrast microscopy on InGaN/GaN quantum well structures. Physica Status Solidi (B): Basic Research, 2016, 253, 140-144.	1.5	31
36	On-chip beamsplitter operation on single photons from quasi-resonantly excited quantum dots embedded in GaAs rib waveguides. Applied Physics Letters, 2015, 107, .	3.3	30

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37	Generation, guiding and splitting of triggered single photons from a resonantly excited quantum dot in a photonic circuit. Optics Express, 2016, 24, 3089.	3.4	30
38	Two-photon interference in an atomâ€"quantum dot hybrid system. Optica, 2018, 5, 367.	9.3	29
39	Single-photon emission from a type-B InPâˆ•GaInP quantum dot. Journal of Applied Physics, 2005, 98, 093522.	2.5	27
40	Triggered single-photon emission from electrically excited quantum dots in the red spectral range. Applied Physics Letters, 2010, 97, .	3.3	27
41	Low-noise quantum frequency down-conversion of indistinguishable photons. Optics Express, 2016, 24, 22250.	3.4	27
42	Deterministic fabrication of circular Bragg gratings coupled to single quantum emitters via the combination of <i>in-situ</i> optical lithography and electron-beam lithography. Journal of Applied Physics, 2019, 125, .	2.5	27
43	3D printed micro-optics for quantum technology: Optimised coupling of single quantum dot emission into a single-mode fibre. Light Advanced Manufacturing, 2021, 2, 103.	5.1	26
44	Red to green photoluminescence of InP-quantum dots in InP. Journal of Crystal Growth, 2007, 298, 595-598.	1.5	25
45	Short wavelength red-emitting AlGaInP-VECSEL exceeds 1.2â€‰W continuous-wave output power. Applied Physics B: Lasers and Optics, 2011, 102, 789-794.	2.2	25
46	High-power InP quantum dot based semiconductor disk laser exceeding 1.3â€‰W. Applied Physics Letters, 2013, 102, .	3.3	25
47	Lasing properties of InP/(Ga<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML") Tj ETQq1 1 0.784314 rgBT /Overlock 10 quantu	3.2	24
48	25â€‰â€‰W continuous wave output at 665â€‰â€‰nm from a multipass and quantum-well-pumped AlGaInP vertical-external-cavity surface-emitting laser. Optics Letters, 2016, 41, 1245.	3.3	24
49	Room-temperature lasing of electrically pumped red-emitting InP/(Al0.20Ga0.80)0.51In0.49P quantum dots embedded in a vertical microcavity. Applied Physics Letters, 2009, 95, .	3.3	23
50	DBRâ€free semiconductor disc laser on SiC heatspreader emitting 10.1 W at 1007Ânm. Electronics Letters, 2017, 53, 1537-1539.	1.0	23
51	Wavelength tunable ultraviolet laser emission via intra-cavity frequency doubling of an AlGaInP vertical external-cavity surface-emitting laser down to 328â€‰nm. Applied Physics Letters, 2011, 99, .	3.3	22
52	Intra-cavity frequency-doubled mode-locked semiconductor disk laser at 325 nm. Optics Express, 2015, 23, 19947.	3.4	22
53	High wavelength tunability of InGaN quantum wells grown on semipolar GaN pyramid facets. Physica Status Solidi (B): Basic Research, 2011, 248, 605-610.	1.5	21
54	Spectroscopy of the<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi>D</mml:mi><mml:mn>1</mml:mn></mml:msub></mml:m of cesium by dressed-state resonance fluorescence from a single (In,Ga)As/GaAs quantum dot. Physical Review B, 2014, 90, .	3.2	21

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55	Neutral and charged biexciton-exciton cascade in near-telecom-wavelength quantum dots. Physical Review B, 2016, 94, .	3.2	21
56	Time- and locally resolved photoluminescence of semipolar GaInNâˆ•GaN facet light emitting diodes. Applied Physics Letters, 2007, 90, 171123.	3.3	20
57	Thin-film InGaAs metamorphic buffer for telecom C-band InAs quantum dots and optical resonators on GaAs platform. Nanophotonics, 2022, 11, 1109-1116.	6.0	20
58	Electric-Field Tuning of Spin-Dependent Exciton-Exciton Interactions in Coupled Quantum Wells. Physical Review Letters, 1999, 83, 2433-2436.	7.8	19
59	Structural and emission properties of InGaAs/GaAs quantum dots emitting at 1.3â€‰Î¼m. Applied Physics Letters, 2014, 105, 152102.	3.3	19
60	High optical output power in the UVA range of a frequency-doubled, strain-compensated AlGaInP-VECSEL. Applied Physics Express, 2014, 7, 092705.	2.4	19
61	Resonance fluorescence of single In(Ga)As quantum dots emitting in the telecom C-band. Applied Physics Letters, 2021, 118, .	3.3	19
62	Optical charge injection and coherent control of a quantum-dot spin-qubit emitting at telecom wavelengths. Nature Communications, 2022, 13, 748.	12.8	19
63	Enhanced efficiency of AlGaInP disk laser by in-well pumping. Optics Express, 2015, 23, 2472.	3.4	18
64	Single-photon and photon pair emission from MOVPE-grown In(Ga)As quantum dots: shifting the emission wavelength from 1.0 to 1.3Âμm. Applied Physics B: Lasers and Optics, 2016, 122, 1.	2.2	18
65	Temperature-dependent properties of single long-wavelength InGaAs quantum dots embedded in a strain reducing layer. Journal of Applied Physics, 2017, 121, 184302.	2.5	18
66	Chem/bio sensing with non-classical light and integrated photonics. Analyst, The, 2018, 143, 593-605.	3.5	18
67	Triggered single-photon emission in the red spectral range from optically excited InP/(Al,Ga)InP quantum dots embedded in micropillars up to 100 K. Journal of Applied Physics, 2011, 110, 063108.	2.5	17
68	Optical Gain and Lasing Properties of InP/AlGaInP Quantum-Dot Laser Diode Emitting at 660 nm. IEEE Journal of Quantum Electronics, 2019, 55, 1-7.	1.9	17
69	Nonresonant tunneling in single asymmetric pairs of vertically stackedInPquantum dots. Physical Review B, 2007, 76, .	3.2	16
70	Mollow quintuplets from coherently excited quantum dots. Optics Letters, 2013, 38, 1691.	3.3	16
71	Purcell-enhanced single-photon emission from a strain-tunable quantum dot in a cavity-waveguide device. Applied Physics Letters, 2020, 117, .	3.3	16
72	Bragg grating cavities embedded into nano-photonic waveguides for Purcell enhanced quantum dot emission. Optics Express, 2018, 26, 30614.	3.4	16

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73	Microcavity-enhanced Kerr nonlinearity in a vertical-external-cavity surface-emitting laser. Optics Express, 2019, 27, 11914.	3.4	16
74	Quantum dot-based broadband optical antenna for efficient extraction of single photons in the telecom O-band. Optics Express, 2020, 28, 19457.	3.4	16
75	Red VCSEL for high-temperature applications. Journal of Crystal Growth, 2004, 272, 549-554.	1.5	15
76	Postselected indistinguishable single-photon emission from the Mollow triplet sidebands of a resonantly excited quantum dot. Physical Review B, 2013, 87, .	3.2	15
77	Self-mode-locked AlGaInP-VECSEL. Applied Physics Letters, 2017, 111, .	3.3	15
78	Overcoming correlation fluctuations in two-photon interference experiments with differently bright and independently blinking remote quantum emitters. Physical Review B, 2018, 97, .	3.2	15
79	Low Threshold InP/AlGaInP Quantum Dot In-Plane Laser Emitting at 638 nm. Applied Physics Express, 2009, 2, 112501.	2.4	14
80	All quantum dot mode-locked semiconductor disk laser emitting at 655â€‰nm. Applied Physics Letters, 2014, 105, .	3.3	14
81	Selective growth of GaInN quantum dot structures. Journal of Crystal Growth, 2004, 272, 204-210.	1.5	13
82	Characterisation of quaternary AlInGaN thick layers and quantum wells grown by MOVPE. Journal of Crystal Growth, 2004, 272, 386-392.	1.5	13
83	Red single-photon emission from an InPâ^•GaInP quantum dot embedded in a planar monolithic microcavity. Applied Physics Letters, 2008, 92, .	3.3	13
84	Low-density InP quantum dots embedded in Ga0.51In0.49P with high optical quality realized by a strain inducing layer. Applied Physics Letters, 2010, 97, 063107.	3.3	13
85	Polarization fine structure and enhanced single-photon emission of self-assembled lateral InGaAs quantum dot molecules embedded in a planar microcavity. Journal of Applied Physics, 2009, 105, 122408.	2.5	12
86	Low density MOVPE grown InGaAs QDs exhibiting ultra-narrow single exciton linewidths. Nanotechnology, 2010, 21, 125606.	2.6	12
87	Spectrally and timeâ€resolved cathodoluminescence microscopy of semipolar InGaN SQW on (11$overline {2} $2) and (10$overline {1} $1) pyramid facets. Physica Status Solidi (B): Basic Research, 2011, 248, 632-637.	1.5	12
88	Laterally Coupled InGaN/GaN DFB Laser Diodes. Physica Status Solidi A, 2002, 192, 301-307.	1.7	11
89	Electron and hole spins in InP/(Ga,In)P self-assembled quantum dots. Physical Review B, 2012, 86, .	3.2	10
90	Single-photon emission from electrically driven InP quantum dots epitaxially grown on CMOS-compatible Si(001). Nanotechnology, 2012, 23, 335201.	2.6	10

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91	Strain compensation techniques for red AlGaInP-VECSELs: Performance comparison of epitaxial designs. Journal of Crystal Growth, 2013, 370, 208-211.	1.5	10
92	Pure single-photon emission from In(Ga)As QDs in a tunable fiber-based external mirror microcavity. Quantum Science and Technology, 2018, 3, 034009.	5.8	10
93	Investigations on local Ga and In incorporation of GaInN quantum wells on facets of selectively grown GaN stripes. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1587-1590.	0.8	9
94	Vertical asymmetric double quantum dots. Journal of Crystal Growth, 2007, 298, 603-606.	1.5	9
95	Transverse-Mode Analysis of Red-Emitting Highly Polarized Vertical-Cavity Surface-Emitting Lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2011, 17, 724-729.	2.9	9
96	Quaternary AlxInyGa1â^'xâ^'yN layers deposited by pulsed metal-organic vapor-phase epitaxy for high efficiency light emission. Journal of Crystal Growth, 2011, 315, 254-257.	1.5	9
97	Strong antibunching from electrically driven devices with long pulses: A regime for quantum-dot single-photon generation. Physical Review B, 2012, 86, .	3.2	9
98	Strong mode coupling in InP quantum dot-based GaInP microdisk cavity dimers. New Journal of Physics, 2013, 15, 013060.	2.9	9
99	Characterization of a Photon-Number Resolving SNSPD Using Poissonian and Sub-Poissonian Light. IEEE Transactions on Applied Superconductivity, 2019, 29, 1-5.	1.7	9
100	Characterization of spectral diffusion by slow-light photon-correlation spectroscopy. Physical Review B, 2020, 101, .	3.2	9
101	Evidence of different confinement regimes in site-controlled pyramidal InGaN structures. Physica Status Solidi (B): Basic Research, 2005, 242, R97-R99.	1.5	8
102	Excited-state spectroscopy of single lateral self-assembled InGaAs quantum dot molecules. Physical Review B, 2012, 85, .	3.2	8
103	Vertically stacked and laterally ordered InP and In(Ga)As quantum dots for quantum gate applications. Physica Status Solidi (B): Basic Research, 2012, 249, 737-746.	1.5	8
104	Comparison of AlGaInP-VECSEL gain structures. Journal of Crystal Growth, 2015, 414, 219-222.	1.5	8
105	Single-photon light-emitting diodes based on preselected quantum dots using a deterministic lithography technique. Applied Physics Letters, 2019, 114, .	3.3	8
106	Achieving stable fiber coupling of quantum dot telecom C-band single-photons to an SOI photonic device. Applied Physics Letters, 2021, 119, .	3.3	8
107	Integrated Optoelectronic Devices Using Labâ€Onâ€Fiber Technology. Advanced Materials Technologies, 2022, 7, .	5.8	8
108	Pulsed single-photon resonant-cavity quantum dot LED. Journal of Crystal Growth, 2011, 315, 127-130.	1.5	7

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109	Signatures of single-photon interaction between two quantum dots located in different cavities of a weakly coupled double microdisk structure. Physical Review B, 2018, 97, .	3.2	7
110	Tuning emission energy and fine structure splitting in quantum dots emitting in the telecom O-band. AIP Advances, 2019, 9, .	1.3	7
111	Time-resolved and single dot spectroscopy of type II InP/GaInP quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1197-1200.	0.8	6
112	160Â°C pulsed laser operation of AlGaInP-based vertical-cavity surface-emitting lasers. Electronics Letters, 2003, 39, 1654.	1.0	6
113	Selective growth of GaInN quantum dot structures. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 133-137.	2.7	6
114	Red to orange electroluminescence from InP/AlGaInP quantum dots at room temperature. Journal of Crystal Growth, 2008, 310, 5098-5101.	1.5	6
115	Optical studies of GaInP/GaP quantum dots. Journal of Luminescence, 2003, 102-103, 1-6.	3.1	5
116	Red VCSEL for automotive applications. , 2005, , .		5
117	Transport of laser accelerated proton beams and isochoric heating of matter. Journal of Physics: Conference Series, 2010, 244, 012009.	0.4	5
118	Optical properties of red emitting self-assembled InP/(Al_020Ga_080)_051In_049P quantum dot based micropillars. Optics Express, 2010, 18, 12543.	3.4	5
119	The phase boundary of superconducting niobium thin films with antidot arrays fabricated with microsphere photolithography. Superconductor Science and Technology, 2012, 25, 065020.	3.5	5
120	Optical investigations on single vertically coupled InP/GaInP quantum dot pairs. Physica Status Solidi (B): Basic Research, 2012, 249, 747-751.	1.5	5
121	Controllable Delay and Polarization Routing of Single Photons. Advanced Quantum Technologies, 2020, 3, 1900057.	3.9	5
122	Stable fundamental and dual-pulse mode locking of red-emitting VECSELs. Laser Physics Letters, 2020, 17, 065001.	1.4	5
123	Realization of a tunable fiber-based double cavity system. Physical Review B, 2020, 102, .	3.2	5
124	In-Redistribution in a GaInN Quantum Well upon Thermal Annealing. Physica Status Solidi (B): Basic Research, 2002, 234, 738-741.	1.5	4
125	Initial Experiments to Obtain Self-Assembled GaInN Quantum Islands by MOVPE. Physica Status Solidi A, 2002, 192, 412-416.	1.7	4
126	Increased single-photon emission from InP/AlGaInP quantum dots grown on AlGaAs distributed Bragg reflectors. Journal of Crystal Growth, 2008, 310, 4818-4820.	1.5	4

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127	Low threshold electrically pumped red emitting InP/Al<inf>0.20</inf>GaInP quantum dot vertical microcavity laser. , 2009, , .		4
128	InP quantum dots for applications in laser devices and future solid-state quantum gates. Journal of Physics: Conference Series, 2010, 245, 012077.	0.4	4
129	Red AlGaInP-VECSEL emitting at around 665 nm: strain compensation and performance comparison of different epitaxial designs. Proceedings of SPIE, 2012, , .	0.8	4
130	Site-controlled growth of InP/GaInP islands on periodic hole patterns in GaAs substrates produced by microsphere photolithography. Journal of Crystal Growth, 2013, 370, 146-149.	1.5	4
131	Optical studies of GaxIn1-xP/Ga0.5In0.5P quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1225-1228.	0.8	3
132	Regions of Different Confinement in Low-Dimensional AlyInxGa1âˆ’xâˆ’yN Quantum Structures. Advances in OptoElectronics, 2007, 2007, 1-6.	0.6	3
133	Wavelength tunable red AlGaInP-VECSEL emitting at around 660 nm. Proceedings of SPIE, 2011, , .	0.8	3
134	Growth and characterization of electrically pumped red-emitting VCSEL with embedded InP/AlGaInP quantumdots. Journal of Crystal Growth, 2011, 315, 131-133.	1.5	3
135	MOVPE grown quaternary AlInGaN layers for polarization matched quantum wells and efficient active regions. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2163-2166.	0.8	3
136	Influence of the oxide aperture radius on the mode spectra of (Al,Ga)As vertical microcavities with electrically excited InP quantum dots. Applied Physics Letters, 2013, 102, .	3.3	3
137	Active and Passive LC Based Polarization Elements. Molecular Crystals and Liquid Crystals, 2014, 594, 140-149.	0.9	3
138	Quantum dot based mode-locked AlGaInP-VECSEL. Proceedings of SPIE, 2015, , .	0.8	3
139	Gain chip design, power scaling and intra-cavity frequency doubling with LBO of optically pumped red-emitting AlGaInP-VECSELs. , 2016, , .		3
140	Semiconductor Quantum Dots for Integrated Quantum Photonics (Adv. Quantum Technol. 9/2019). Advanced Quantum Technologies, 2019, 2, 1970053.	3.9	3
141	Wavelength and Pump-Power Dependent Nonlinear Refraction and Absorption in a Semiconductor Disk Laser. IEEE Photonics Technology Letters, 2020, 32, 85-88.	2.5	3
142	Gaussian-like transverse-mode profile characteristics of high-power large-area red-emitting VCSELs. Optics Letters, 2020, 45, 1419.	3.3	3
143	High-power quasi-CW diode-pumped 750-nm AlGaAs VECSEL emitting a peak power of 29.6â€…W and an average power of 8.5â€…W. Optics Letters, 2022, 47, 1980.	3.3	3
144	Optical investigations on InP and GaInP quantum dots. , 0, , .		2

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145	Photoluminescence Studies on InGaN/GaN Quantum Dots. Physica Status Solidi A, 2002, 192, 91-96.	1.7	2
146	Analysis of the modulation behavior of red VCSELs. , 2004, 5597, 102.		2
147	Growth of self-assembled AlInGaN quantum dots by MOVPE. Journal of Crystal Growth, 2004, 272, 186-191.	1.5	2
148	Structural and optical characterization of AlyInxGa1â€“x â€“yN quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 2073-2077.	0.8	2
149	Pulsed layer growth of AlInGaN nanostructures. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1491-1494.	0.8	2
150	Non-resonant tunneling in single pairs of vertically stacked asymmetric InP/GaInP quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1958-1960.	2.7	2
151	InP-quantum dots in Al0.20Ga0.80InP with different barrier configurations. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 906-909.	0.8	2
152	InP quantum dots in pillar microcavities â€" mode spectra and single-photon emission. Journal of Physics: Conference Series, 2010, 210, 012010.	0.4	2
153	Spectral features in different sized InGaN/GaN micropyramids. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2387-2389.	0.8	2
154	Generation of UV laser light via intra-cavity frequency doubling of an AlGaInP-VECSEL. , 2011, , .		2
155	Frequency doubled AlGaInP-VECSEL with high output power at 331 nm and a large wavelength tuning range in the UV. , 2012, , .		2
156	UV laser emission around 330 nm via intracavity frequency doubling of a tunable red AlGaInP-VECSEL. , 2012, , .		2
157	Epitaxially Grown Indium Phosphide Quantum Dots on a Virtual Ge Substrate Realized on Si(001). Applied Physics Express, 2012, 5, 042001.	2.4	2
158	Femtosecond mode-locked red AlGaInP-VECSEL. Proceedings of SPIE, 2014, , .	0.8	2
159	Defect reduced selectively grown GaN pyramids as template for green InGaN quantum wells. Physica Status Solidi (B): Basic Research, 2016, 253, 67-72.	1.5	2
160	Efficiency and power scaling of in-well and multi-pass pumped AlGaInP VECSELs. Proceedings of SPIE, 2016, , .	0.8	2
161	The optically pumped semiconductor membrane external-cavity surface-emitting laser (MECSEL): a concept based on a diamond-sandwiched active region. , 2017, , .		2
162	InGaAsP VECSEL for watt-level output at a wavelength around 765â€‰nm. Optics Letters, 2022, 47, 2178.	3.3	2

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163	Red surface emitters: powerful and fast. , 2003, , .		1
164	Study of as deposited metal contacts for n-SiC. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 2533-2536.	0.8	1
165	Analog Modulation of 650-nm VCSELs. IEEE Photonics Technology Letters, 2006, 18, 583-585.	2.5	1
166	Carrier dynamics in site-controlled Ga1â€“xInxN quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 2060-2064.	0.8	1
167	Red high-temperature AlGaInP-VCSEL. , 2007, , .		1
168	Growth of red InP/GaInP quantum dots on a low density InAs/GaAs island seed layer by MOVPE. Journal of Crystal Growth, 2008, 310, 5089-5092.	1.5	1
169	DC and pulsed electrical excitation of single quantum dots. Proceedings of SPIE, 2010, , .	0.8	1
170	Transverse mode and polarization characteristics of AlGaInP-based VCSELs with integrated multiple oxide apertures. Proceedings of SPIE, 2012, , .	0.8	1
171	Direct imaging of GaN Pyramids covered by InGaN Single Quantum Well using nano-scale Scanning Transmission Electron Microscopy Cathodoluminescence. Microscopy and Microanalysis, 2012, 18, 1838-1839.	0.4	1
172	Fabrication and optical characterization of large scale membrane containing InP/AlGaInP quantum dots. Nanotechnology, 2015, 26, 235201.	2.6	1
173	Schemes for efficient QW pumping of AlGaInP disk lasers. Proceedings of SPIE, 2017, , .	0.8	1
174	Microcavity-enhanced Kerr nonlinearity in a vertical-external-cavity surface-emitting laser: erratum. Optics Express, 2021, 29, 23290.	3.4	1
175	Single-photon and polarization-entangled photon emission from InAs quantum dots in the telecom C-band. , 2018, , .		1
176	Development of electrically pumped VECSEL in the visible spectrum. , 2019, , .		1
177	Subthreshold Spectral Bi-Modality of Double Layer InP/AlGaInP Quantum Dot Laser. , 2021, , .		1
178	Non-equilibrium spin noise spectroscopy of a single quantum dot operating at fiber telecommunication wavelengths. Journal of Applied Physics, 2022, 131, 065703.	2.5	1
179	Spin-Dependent Exciton-Exciton Interaction in Quantum Wells under an Electric Field. Physica Status Solidi (B): Basic Research, 1999, 215, 223-228.	1.5	0
180	Optically Induced Stark Shift in DFB Resonators. Physica Status Solidi (B): Basic Research, 1999, 215, 269-273.	1.5	0

#	Article	IF	Citations
181	Comparison of the material properties of GaInN structures grown with ammonia and dimethyl-hydrazine as nitrogen precursors. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2145-2149.	0.8	0
182	Red light VCSEL for high-temperature applications. , 2004, 5594, 141.		0
183	Technology transfer of (Ga)InP-quantum dots. , 0, , .		0
184	Temperature Dependent Photoluminescence Measurements of Single InP Quantum Dots. AIP Conference Proceedings, 2007, , .	0.4	0
185	Green photoluminescence of single InP-quantum dots grown on InP/AlInP distributed Bragg reflectors. Journal of Crystal Growth, 2007, 298, 599-602.	1.5	0
186	Low threshold and room-temperature lasing of electrically pumped red-emitting InP/(Al0.20Ga0.80)0.51In0.49P quantum dots. Journal of Physics: Conference Series, 2010, 210, 012009.	0.4	0
187	MOVPE grown InGaAs quantum dots of high optical quality as seed layer for low-density InP quantum dots. Journal of Physics: Conference Series, 2010, 245, 012009.	0.4	0
188	Influence of the Exciton Dark State on the Optical and Quantum Optical Properties of Single Quantum Dots. , 2010, , .		0
189	Electrically pumped single-photon emission up to 80 Kâ€"Towards a commercial single-photon emitting device. , 2010, , .		0
190	Smooth transition into stimulated emission of InP quantum dots based high-Q microdisk cavities. Journal of Physics: Conference Series, 2010, 210, 012008.	0.4	0
191	5 GHz modulation of 650 nm VCSEL. , 2011, , .		0
192	AlGaInP-based Vertical-Cavity Surface-Emitting Lasers for Sensoring and Polarization Switching. , 2011, , .		0
193	High-frequency Triggered Singleâ€"Photon Emission From Electrically Driven InPâˆ•(Al,Ga)InP Quantum Dots. AIP Conference Proceedings, 2011, , .	0.4	0
194	Approaches for IIIâˆ•V Photonics on Si. AIP Conference Proceedings, 2011, , .	0.4	0
195	High-frequency electrically driven quantum dot single-photon source. , 2011, , .		0
196	Red Emitting VCSEL. Springer Series in Optical Sciences, 2013, , 379-401.	0.7	0
197	Quantum frequency conversion of visible single photons from a quantum dot to a telecom band. , 2013, , .		0
198	InP quantum dot based semiconductor disk laser emitting at 655 nm. , 2013, , .		0

#	Article	IF	Citations
199	SESAM mode-locked red AlGaInP semiconductor disk laser emitting at 665 nm. , 2013, , .		0
200	Thin-film mid-infrared semiconductor waveguide technology. , 2014, , .		0
201	Degradation studies and pump optimization of optically pumped red-emitting AlGaInP-VECSELs. , 2015, , .		0
202	Improved gain chip holder design for high efficient, high power AlGaInP-VECSEL. , 2017, , .		0
203	Quantitative STEM: Comparative Studies of Composition and Optical Properties of Semiconductor Quantum Structures. Microscopy and Microanalysis, 2017, 23, 1690-1691.	0.4	0
204	Quantum dots interfaced with alkali atoms: Filtering, delaying and quantum interfering single photons. , 2017, , .		0
205	Towards InP-based QD-VCSELs emitting at 633 nm. , 2017, , .		0
206	Semiconductor membrane laser concept (MECSEL) applicable to various materials towards new emission wavelengths. , 2017, , .		0
207	Mode-locked red-emitting VECSELs. , 2017, , .		0
208	Influence of Spacer Thickness on the Optical Properties of Vertically Stacked InP/AlGaInP Quantum Dot Lasers at the Short Wavelength. , 2019, , .		0
209	Delaying two-photon Fock states in hot cesium vapor using single photons generated on demand from a semiconductor quantum dot. Physical Review B, 2021, 103, .	3.2	0
210	High-Power Quasi-CW Diode-Pumped 750â€¯nm VECSEL Emitting a Peak Power of 29.6â€¯W and an Average Power of 8.5â€¯W. , 2021, , .		0
211	Efficient and stable fiber-to-chip coupling enabling the injection of telecom quantum dot photons into a silicon photonic chip. , 2021, , .		0
212	Investigation of Resonance Fluorescence in the Telecom C-Band from In(Ga)As Quantum Dots. , 2021, , .		0
213	Quantum Frequency Down-Conversion of Single Photons from a Quantum Dot to the Telecom Band. , 2012, , .		0
214	Photons on demand from an electrically driven single quantum dot under pulsed excitation. , 2012, , .		0
215	Photonic Integrated Circuits with Quantum Dots. Nano-optics and Nanophotonics, 2017, , 409-441.	0.2	0
216	Simultaneous filtering of the Mollow triplet sidebands via a Cs-based Faraday filter. , 2017, , .		0

#	Article	IF	Citations
217	InP/AlGaInP quantum dot laser emitting at short wavelength of 660 nm. , 2019, , .		0
218	Investigations on the origins of self-mode-locking in Vertical-External-Cavity Surface-Emitting-Lasers: Nonlinear lensing and the role of the microcavity. , 2019, , .		0
219	Direct Imaging of the Carrier Capture into Individual InP Quantum Dots of a Semiconductor Disk Laser Membrane. ACS Nano, 2022, 16, 4619-4628.	14.6	0
220	Quantum Optical Studies of Single Coupled Quantum Dot Pairs. , 0, , 33-51.		0